

Access DB# 129713**SEARCH REQUEST FORM**

Scientific and Technical Information Center

Requester's Full Name: Sin J. Lee Examiner #: 76060 Date: 8-10-2004  
 Art Unit: 1752 Phone Number 301-21333 Serial Number: 10/721,400  
 Mail Box and Bldg/Room Location: 9D66 Results Format Preferred (circle) PAPER DISK E-MAIL

If more than one search is submitted, please prioritize searches in order of need.

\*\*\*\*\*

Please provide a detailed statement of the search topic, and describe as specifically as possible the subject matter to be searched.  
 Include the elected species or structures, keywords, synonyms, acronyms, and registry numbers, and combine with the concept or utility of the invention. Define any terms that may have a special meaning. Give examples or relevant citations, authors, etc, if known. Please attach a copy of the cover sheet, pertinent claims, and abstract.

Title of Invention: photosensitive Polymer containing silicon and a resist composition using the  
 Inventors (please provide full names): Choi, Sang-Jun Sam

Earliest Priority Filing Date: 11-25-03

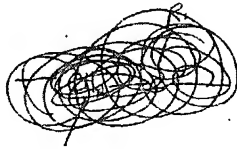
\*For Sequence Searches Only\* Please include all pertinent information (parent, child, divisional, or issued patent numbers) along with the appropriate serial number.

US20040126699

— Please search for the ~~silicon~~ polymer of

Claim # 1

(Please note that  
 all of those repeating  
 units need to be  
 present in the polymer)

\*\*\*\*\*  
STAFF USE ONLY

	Type of Search	Vendors and cost where applicable
Searcher: <u>83 al</u>	NA Sequence (#) <u>STN</u>	
Searcher Phone #: _____	AA Sequence (#) _____	Dialog _____
Searcher Location: _____	Structure (#) <u>Questel/Orbit</u>	
Date Searcher Picked Up: <u>8/19/04</u>	Bibliographic _____	Dr. Link _____
Date Completed: <u>8/19/04</u>	Litigation _____	Lexis/Nexis _____
Searcher Prep & Review Time: <u>40</u>	Fulltext _____	Sequence Systems _____
Clerical Prep Time: _____	Patent Family _____	WWW/Internet _____
Online Time: <u>60</u>	Other _____	Other (specify) _____

=> D HIS

(FILE 'HOME' ENTERED AT 13:41:16 ON 18 AUG 2004)

FILE 'HCA' ENTERED AT 13:41:20 ON 18 AUG 2004  
E US20040126699/PN

L1 1 S E3  
SEL L1 RN

FILE 'REGISTRY' ENTERED AT 13:41:43 ON 18 AUG 2004

L2 8 S E1-E8  
L3 6 S L2 AND PMS/CI

FILE 'LCA' ENTERED AT 13:42:34 ON 18 AUG 2004

FILE 'HCA' ENTERED AT 13:42:58 ON 18 AUG 2004

FILE 'LREGISTRY' ENTERED AT 13:43:04 ON 18 AUG 2004

FILE 'REGISTRY' ENTERED AT 14:39:10 ON 18 AUG 2004

L4 2 S 110-31-6/CRN  
L5 23104 S 108-31-6/CRN

FILE 'LREGISTRY' ENTERED AT 14:40:41 ON 18 AUG 2004

L6 STR  
L7 STR L6  
L8 STR L6  
L9 SCR 2043

FILE 'REGISTRY' ENTERED AT 14:48:16 ON 18 AUG 2004

L10 50 S L7 AND L8  
L11 12 S L10 AND L5  
L12 1092 S L7 AND L8 FULL  
SAVE LEE400/A L12  
L13 271 S L12 AND L5

FILE 'HCA' ENTERED AT 14:50:41 ON 18 AUG 2004

L14 145 S L13  
L15 145 S L14 AND 1907-2003/PY,PRY  
L16 1597405 S PHOTSENSIT? OR PHOTOPOLYM? OR PHOTORESIST? OR PHOTOCHEM? OR  
L17 116 S L15 AND L16

FILE 'REGISTRY' ENTERED AT 14:52:15 ON 18 AUG 2004

L18 86 S L13 AND 3-4/NC

FILE 'LREGISTRY' ENTERED AT 14:54:14 ON 18 AUG 2004

FILE 'REGISTRY' ENTERED AT 14:55:01 ON 18 AUG 2004

L19 50 S L7 SSS SAM SUB=L12

FILE 'LREGISTRY' ENTERED AT 14:56:17 ON 18 AUG 2004

L20 STR L8

FILE 'REGISTRY' ENTERED AT 14:58:12 ON 18 AUG 2004

L21 0 S L7 AND L20 SSS SAM SUB=L12  
L22 STR L20  
L23 6 S L7 AND L22 SSS SAM SUB=L12  
L24 125 S L7 AND L22 SSS FULL SUB=L12

SAVE L24 LEE400A/A  
L25 6 S L24 AND L5  
L26 9 S L25 OR L3  
L27 3 S L26 NOT L25

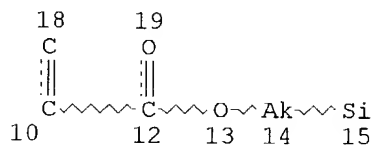
FILE 'HCA' ENTERED AT 15:05:39 ON 18 AUG 2004  
L28 3 S L26  
L29 3 S L28 AND L16

FILE 'LREGISTRY' ENTERED AT 15:06:24 ON 18 AUG 2004

FILE 'REGISTRY' ENTERED AT 15:20:05 ON 18 AUG 2004

=> D QUE STAT 124

L7 STR



NODE ATTRIBUTES:

DEFAULT MLEVEL IS ATOM

DEFAULT ECLEVEL IS LIMITED

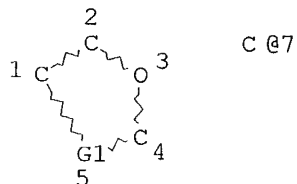
GRAPH ATTRIBUTES:

RING(S) ARE ISOLATED OR EMBEDDED

NUMBER OF NODES IS 7

STEREO ATTRIBUTES: NONE

L8 STR



REP G1=(1-4) 7

NODE ATTRIBUTES:

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DEFAULT ECLEVEL IS LIMITED

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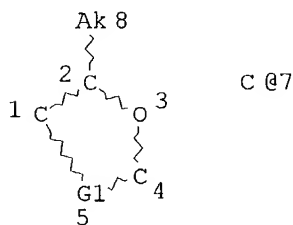
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NUMBER OF NODES IS 6

STEREO ATTRIBUTES: NONE

L12 1092 SEA FILE=REGISTRY SSS FUL L7 AND L8

L22-----STR-----



REP G1=(1-4) 7  
NODE ATTRIBUTES:  
DEFAULT MLEVEL IS ATOM  
DEFAULT ECLEVEL IS LIMITED

GRAPH ATTRIBUTES:  
RING(S) ARE ISOLATED OR EMBEDDED  
NUMBER OF NODES IS 7

STEREO ATTRIBUTES: NONE  
L24 125 SEA FILE=REGISTRY SUB=L12 SSS FUL L7 AND L22

100.0% PROCESSED 1092 ITERATIONS 125 ANSWERS  
SEARCH TIME: 00.00.01

=> FILE HCA  
FILE 'HCA' ENTERED AT 15:20:34 ON 18 AUG 2004  
USE IS SUBJECT TO THE TERMS OF YOUR STN CUSTOMER AGREEMENT.  
PLEASE SEE "HELP USAGETERMS" FOR DETAILS.  
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FILE COVERS 1907 - 13 Aug 2004 VOL 141 ISS 8  
FILE LAST UPDATED: 13 Aug 2004 (20040813/ED)

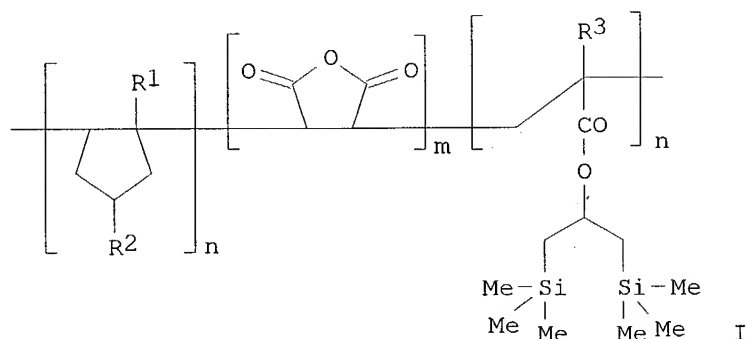
This file contains CAS Registry Numbers for easy and accurate substance identification.

=> D-129-1-3 IBIB-ABS-HITIND-HITSTR

L29 ANSWER 1 OF 3 HCA COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 141:96681 HCA  
TITLE: Photosensitive polymer containing silicon  
for resist composition

INVENTOR(S): Choi, Sang-Jun  
 PATENT ASSIGNEE(S): Samsung Electronics Co., Inc., S. Korea  
 SOURCE: U.S. Pat. Appl. Publ., 7 pp.  
 CODEN: USXXCO  
 DOCUMENT TYPE: Patent  
 LANGUAGE: English  
 FAMILY ACC. NUM. COUNT: 1  
 PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
US 2004126699	A1	20040701	US 2003- <u>721400</u>	20031125
PRIORITY APPLN. INFO.: GI			KR 2002-86875	A 20021230



*applicant*

AB A **photosensitive** polymer including silicon and a **resist** composition using the polymer are disclosed. The **photosensitive** polymer has the following formula I (R1, R3 = alkyl; R2 = H, alkyl, alkoxy, carbonyl; x = 1-4; m/(m+n+p) = 0.1-0.4; n/(m+n+p) = 0.1-0.5; p/(m+n+p) = 0.1-0.4). The object of the present invention is to provide a **photosensitive** polymer for a top **photoresist** in a bi-layer **resist** process that has an increase in dry etch **resistance** and adhesive strength as compared to a conventional **photoresist**, and to provide a **resist** composition using the inventive polymer.

IC ICM G03C001-73

ICS G03F007-039

NCL 430270100; 430905000; 430910000; 430914000; 430921000; 430925000

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

ST **photosensitive** polymer silicon **resist** compn

IT **Photolithography**

**Photoresists**

(**photosensitive** polymer containing silicon and **resist** composition)

IT 714274-73-4P 714274-74-5P 714274-75-6P

714274-76-7P 714274-77-8P 714274-78-9P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or engineered material use); PREP (Preparation); USES (Uses)

(**photosensitive** polymer containing silicon and **resist** composition)

IT 1116-40-1, Triisobutylamine 66003-78-9, Triphenylsulfonium triflate

RL: TEM (Technical or engineered material use); USES (Uses)  
(**photosensitive** polymer containing silicon and **resist**  
composition)

IT 714274-73-4P 714274-74-5P 714274-75-6P  
714274-76-7P 714274-77-8P 714274-78-9P

RL: PRP (Properties); SPN (Synthetic preparation); TEM (Technical or  
engineered material use); PREP (Preparation); USES (Uses)  
(**photosensitive** polymer containing silicon and **resist**  
composition)

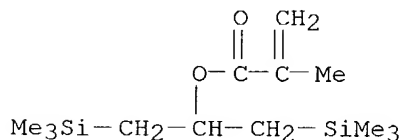
RN 714274-73-4 HCA

CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with 3,4-dihydro-2H-pyran and  
2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 195044-28-1

CMF C13 H28 O2 Si2



CM 2

CRN 110-87-2

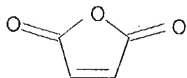
CMF C5 H8 O



CM 3

CRN 108-31-6

CMF C4 H2 O3



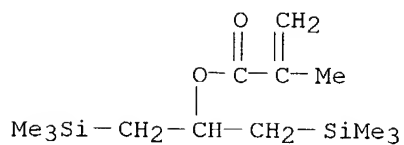
RN 714274-74-5 HCA

CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with 2,3-dihydrofuran and  
2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 195044-28-1

CMF C13 H28 O2 Si2



CM 2

CRN 1191-99-7

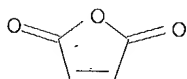
CMF C4 H6 O



CM 3

CRN 108-31-6

CMF C4 H2 O3



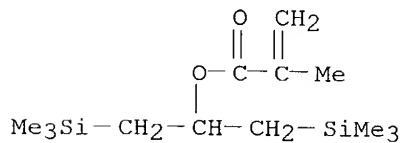
RN 714274-75-6 HCA

CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with 2,3-dihydro-5-  
methylfuran and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

CRN 195044-28-1

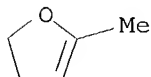
CMF C13 H28 O2 Si2



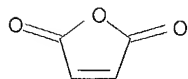
CM 2

CRN 1487-15-6

CMF C5 H8 O

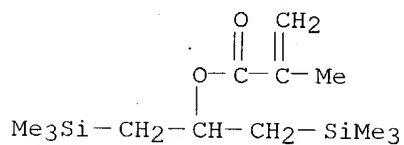


CM 3

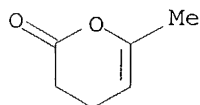
CRN 108-31-6  
CMF C4 H2 O3

RN 714274-76-7 HCA  
CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with 3,4-dihydro-6-methyl-2H-  
pyran-2-one and 2,5-furandione (9CI) (CA INDEX NAME)

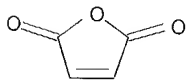
CM 1

CRN 195044-28-1  
CMF C13 H28 O2 Si2

CM 2

CRN 3740-59-8  
CMF C6 H8 O2

CM 3

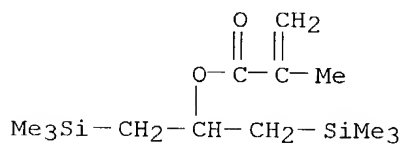
CRN 108-31-6  
CMF C4 H2 O3

RN 714274-77-8 HCA  
CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with 2-ethoxy-3,4-dihydro-6-  
methyl-2H-pyran and 2,5-furandione (9CI) (CA INDEX NAME)

CM 1

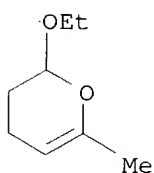


CRN 195044-28-1  
CMF C13 H28 O2 Si2



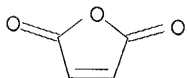
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CRN 52438-71-8  
CMF C8 H14 O2



CM 3

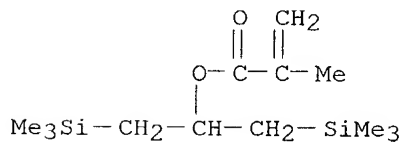
CRN 108-31-6  
CMF C4 H2 O3



RN 714274-78-9 HCA  
CN 2-Propenoic acid, 2-methyl-, 2-(trimethylsilyl)-1-  
[(trimethylsilyl)methyl]ethyl ester, polymer with bicyclo[2.2.1]hept-2-  
ene, 3,4-dihydro-2H-pyran and 2,5-furandione (9CI) (CA INDEX NAME)

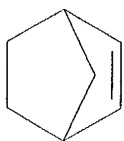
CM 1

CRN 195044-28-1  
CMF C13 H28 O2 Si2



CM 2

CRN 498-66-8  
CMF C7 H10



CM 3

CRN 110-87-2

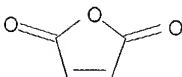
CMF C5 H8 O



CM 4

CRN 108-31-6

CMF C4 H2 O3



L29 ANSWER 2 OF 3 HCA COPYRIGHT 2004 ACS on STN

ACCESSION NUMBER: 137:54616 HCA

TITLE: Positive-working **photoresist** composition for semiconductor device fabrication

INVENTOR(S): Sasaki, Tomoya; Mizutani, Kazuyoshi; Yasunami, Shoichiro

PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan

SOURCE: Jpn. Kokai Tokkyo Koho, 48 pp.

CODEN: JKXXAF

DOCUMENT TYPE: Patent

LANGUAGE: Japanese

FAMILY ACC. NUM. COUNT: 1

PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2002174903	A2	20020621	JP 2000-373077	20001207
PRIORITY APPLN. INFO.:			JP 2000-373077	20001207

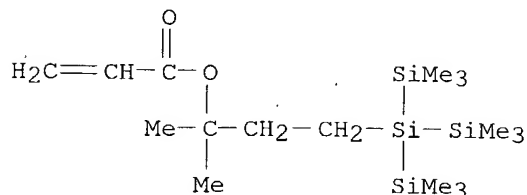
AB The title composition contains a resin increasing solubility in alkaline developer by an

acid and a radiation- or actinic ray -sensitive acid generator, wherein

the resin has repeating unit  $[-COO-C(R_1)(R_2)-\{C(R_3)(R_4)\}_{m_1}-Si(R_5)(R_6)(R_7)-]$ (  $m_1 = 1-6$  integer;  $R_1-2 =$  alkyl;  $R_3-4 =$  H, alkyl;  $R_5-7 =$  alkyl, aryl,allyl, etc.) and  $[-CH_2-C(Y)\{L_2-COO-C(R_1)(R_2)-\{C(R_3)(R_4)\}_{m_1}-$  $Si(R_5)(R_6)(R_7)\}]$  (  $Y =$  H, Me, cyano, Cl;  $m_1 = 1-6$  integer;  $R_1-2 =$  alkyl; $R_3-4 =$  H, alkyl;  $R_5-7 =$  alkyl, aryl, allyl, etc.). The composition provides

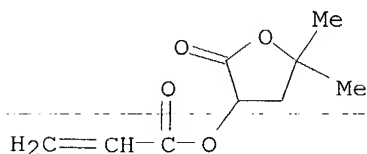
the high resolution and the good pattern edge characteristics.

IC ICM G03F007-039  
ICS C08K005-00; C08K005-42; C08L101-02; G03F007-075; H01L021-027  
CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)  
Section cross-reference(s): 35, 76  
ST pos working **photoresist** compn semiconductor device fabrication  
IT **Photoresists**  
(pos.-working **photoresist** composition for semiconductor device fabrication)  
IT 258341-99-0 260061-58-3 301525-08-6 350251-56-8  
RL: TEM (Technical or engineered material use); USES (Uses)  
(acid generator in pos.-working **photoresist** composition for semiconductor device fabrication)  
IT 438206-85-0 **438206-86-1** 438206-87-2 438206-89-4  
438206-90-7 438206-91-8  
RL: TEM (Technical or engineered material use); USES (Uses)  
(resin in pos.-working **photoresist** composition for semiconductor device fabrication)  
IT **438206-86-1**  
RL: TEM (Technical or engineered material use); USES (Uses)  
(resin in pos.-working **photoresist** composition for semiconductor device fabrication)  
RN 438206-86-1 HCA  
CN 2-Propenoic acid, 1,1-dimethyl-3-[2,2,2-trimethyl-1,1-bis(trimethylsilyl)disilanyl]propyl ester, polymer with 2,5-furandione and tetrahydro-5,5-dimethyl-2-oxo-3-furanyl 2-propenoate (9CI) (CA INDEX NAME)  
  
CM 1  
  
CRN 438206-84-9  
CMF C17 H40 O2 Si4



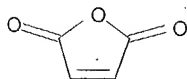
CM 2

CRN 276874-08-9  
CMF C9 H12 O4



CM 3

CRN 108-31-6  
CMF C4 H2 O3



L29 ANSWER 3 OF 3 HCA COPYRIGHT 2004 ACS on STN  
ACCESSION NUMBER: 135:280511 HCA  
TITLE: Positive-working **photoresist** compositions  
showing high resolution and high sensitivity and  
excellent storage stability  
INVENTOR(S): Sato, Kenichiro  
PATENT ASSIGNEE(S): Fuji Photo Film Co., Ltd., Japan  
SOURCE: Jpn. Kokai Tokkyo Koho, 62 pp.  
CODEN: JKXXAF  
DOCUMENT TYPE: Patent  
LANGUAGE: Japanese  
FAMILY ACC. NUM. COUNT: 1  
PATENT INFORMATION:

PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
JP 2001272784	A2	20011005	JP 2000-385724	20001219
PRIORITY APPLN. INFO.:			JP 1999-363302	A 19991221
			JP 2000-10773	A 20000119
			JP 2000-10774	A 20000119

OTHER SOURCE(S): MARPAT 135:280511

AB The compns. contain (A) compds. generating acid on irradiation of actinic ray or radiation, (B) polymers containing structural repeating unit CO<sub>2</sub>CR<sub>1</sub>R<sub>2</sub>(CR<sub>3</sub>R<sub>4</sub>)<sub>m</sub>SiR<sub>5</sub>R<sub>6</sub>R<sub>7</sub> (R<sub>1</sub>-2 = (cyclic) alkyl; R<sub>3</sub>-4 = H, (cyclic) alkyl; R<sub>1</sub> + R<sub>2</sub>, R<sub>3</sub> + R<sub>4</sub> may form cyclic alkyl; R<sub>5</sub>-7 = (cyclic) alkyl, aryl, trialkylsilyl(oxy); m = integer of 1-6) and increasing solubility in alkaline developing agents by reaction with acids, (C) organic basic compds., and (D) ≥1 of F-containing surfactants, Si-containing surfactants, and nonionic surfactants. Preferable structural repeating units also contained in the polymers are given in Markush. Also claimed are (1) compns. consisting of (A') acid-generating sulfonium salts R<sub>s1</sub>S<sup>+</sup> R<sub>s2</sub>R<sub>s3</sub> Z<sup>-</sup> (R<sub>s1</sub>-3 = (un)substituted alkyl or aryl; R<sub>s1</sub> + R<sub>s2</sub> may bond via single bond or bonding group; Z<sup>-</sup> = anion) and polymers B and (2) compns. consisting of acid generators A, polymers B, and certain surfactants given in the document. The compns. are useful in manufacture of semiconductor devices, printed circuits, liquid crystal panels, etc.

IC ICM G03F007-039

ICS C08K005-00; C08L101-08; G03F007-004; G03F007-075; H01L021-027

CC 74-5 (Radiation Chemistry, Photochemistry, and Photographic and Other Reprographic Processes)

Section cross-reference(s): 38

ST pos **photoresist** alk soluble silyl contg polymer; acid generator

pos **photoresist** storage stable; sulfonium salt acid-generator

pos **photoresist**

IT Polysiloxanes, uses

RL: TEM (Technical or engineered material use); USES (Uses)

(KP 341, surfactant; alkaline-developing silyl-containing polymer pos. **photoresists** having storage stability)

IT Positive **photoresists**  
(alkaline-developing silyl-containing polymer pos. **photoresists**  
having storage stability)

IT Sulfonium compounds  
RL: TEM (Technical or engineered material use); USES (Uses)  
(alkaline-developing silyl-containing polymer pos. **photoresists**  
having storage stability)

IT Surfactants  
(fluorosurfactants; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT Surfactants  
(nonionic, surfactant; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT Fluoropolymers, uses  
RL: TEM (Technical or engineered material use); USES (Uses)  
(surfactant; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT 14159-45-6P 39153-56-5P 66003-76-7P 66003-78-9P 67695-82-3P  
138529-81-4P 144089-15-6P 153698-46-5P 177786-98-0P 206861-54-3P  
241806-75-7P 258341-95-6P 258341-99-0P 279218-73-4P 279218-74-5P  
279218-75-6P 301525-08-6P 312386-77-9P 324771-13-3P 350251-56-8P  
350251-57-9P 363616-18-6P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material  
use); PREP (Preparation); USES (Uses)  
(acid generator; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT 263713-67-3P 363616-30-2P 363616-32-4P 363616-34-6P 363616-36-8P  
**363616-38-0P 363616-40-4P** 363616-42-6P 363616-45-9P  
363616-47-1P 363616-49-3P 363616-51-7P 363616-53-9P 363616-56-2P  
363616-59-5P 363616-62-0P 363616-65-3P 363616-68-6P 363616-71-1P  
363616-74-4P 363616-76-6P 363616-77-7P 363616-78-8P 363616-81-3P  
363616-82-4P 363616-83-5P 363616-85-7P 363616-86-8P  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material  
use); PREP (Preparation); USES (Uses)  
(alkaline-developing silyl-containing polymer pos. **photoresists**  
having storage stability)

IT 484-47-9, 2,4,5-Triphenyl imidazole 1122-58-3, 4-Dimethylamino pyridine  
6674-22-2, 1,8-Diazabicyclo[5.4.0]-7-undecene  
RL: TEM (Technical or engineered material use); USES (Uses)  
(alkaline-developing silyl-containing polymer pos. **photoresists**  
having storage stability)

IT 96-48-0,  $\gamma$ -Butyrolactone 96-49-1, Ethylene carbonate 97-64-3,  
Ethyl lactate 108-32-7, Propylene carbonate 110-43-0, 2-Heptanone  
123-86-4, Butyl acetate 1320-67-8, Propylene glycol monomethyl ether  
14272-48-1, 2-Ethoxyethyl propionate 84540-57-8, Propylene glycol  
monomethyl ether acetate 98516-33-7, Propylene glycol monomethyl ether  
propionate  
RL: TEM (Technical or engineered material use); USES (Uses)  
(solvent; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT 9016-45-9, Polyoxyethylene nonylphenyl ether 137462-24-9, Megafac F176  
216679-67-3, Megafac R08 364039-09-8, Troysol S 336  
RL: TEM (Technical or engineered material use); USES (Uses)  
(surfactant; alkaline-developing silyl-containing polymer pos.  
**photoresists** having storage stability)

IT **363616-38-0P 363616-40-4P**  
RL: PNU (Preparation, unclassified); TEM (Technical or engineered material  
use); PREP (Preparation); USES (Uses)

(alkaline-developing silyl-containing polymer pos. photoresists  
having storage stability)

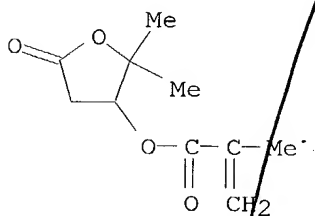
RN 363616-38-0 HCA

CN 2-Propenoic acid, 2-methyl-, polymer with 1,1-dimethyl-3-[2,2,2-trimethyl-  
1,1-bis(trimethylsilyl)disilanyl]propyl 2-methyl-2-propenoate,  
2,5-furandione and tetrahydro-2,2-dimethyl-5-oxo-3-furanyl  
2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 324761-31-1

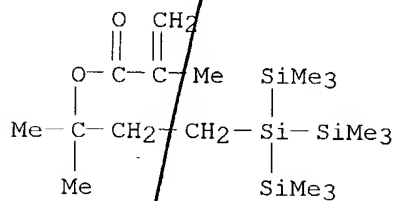
CMF C10 H14 O4



CM 2

CRN 250588-94-4

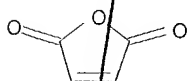
CMF C18 H42 O2 Si4



CM 3

CRN 108-31-6

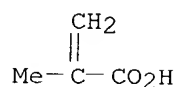
CMF C4 H2 O3



CM 4

CRN 79-41-4-

CMF C4 H6 O2



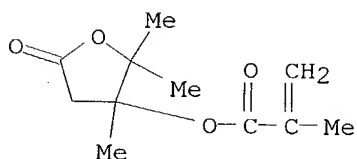
RN 363616-40-4 HCA

CN 2-Propenoic acid, 2-methyl-, 1,1-dimethyl-3-[2,2,2-trimethyl-1,1-bis(trimethylsilyl)disilanyl]propyl ester, polymer with 2,5-furandione, 2-methyl-N-(methylsulfonyl)-2-propenamide and tetrahydro-2,2,3-trimethyl-5-oxo-3-furanyl 2-methyl-2-propenoate (9CI) (CA INDEX NAME)

CM 1

CRN 324761-27-5

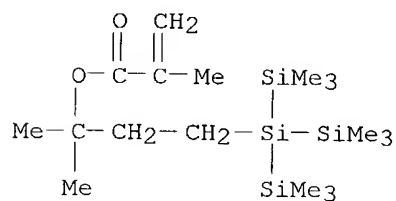
CMF C11 H16 O4



CM 2

CRN 250588-94-4

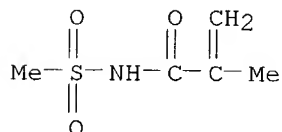
CMF C18 H42 O2 Si4



CM 3

CRN 208761-54-0

CMF C5 H9 N O3 S



CM 4

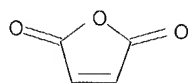
CRN 108-31-6

CMF C4 H2 O3

Sin Lee

10/721,400

08/18/2004



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